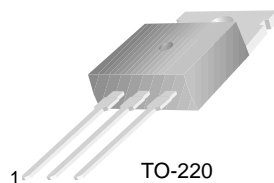


FJP5027

High Voltage and High Reliability

- High Speed Switching
- Wide SOA



TO-220
1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	3	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	1.5	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}, I_E = 0$	1100			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	800			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}, I_C = 0$	7			V
$V_{CEX(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 1.5\text{A}, I_{B1} = -I_{B2} = 0.3\text{A}$ $L = 2\text{mH}, \text{Clamped}$	800			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 800\text{V}, I_E = 0$			10	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			10	μA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 0.2\text{A}$ $V_{CE} = 5\text{V}, I_C = 1\text{A}$	10 8		40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.5\text{A}, I_B = 0.3\text{A}$			2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1.5\text{A}, I_B = 0.3\text{A}$			1.5	V
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		60		pF
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.2\text{A}$		15		MHz
t_{ON}	Turn On Time	$V_{CC} = 400\text{V}$			0.5	μs
t_{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 2\text{A}$			3	μs
t_F	Fall Time	$R_L = 200\Omega$			0.3	μs

h_{FE} Classification

Classification	N	R	O
h_{FE1}	10 ~ 20	15 ~ 30	20 ~ 40

Typical Characteristics

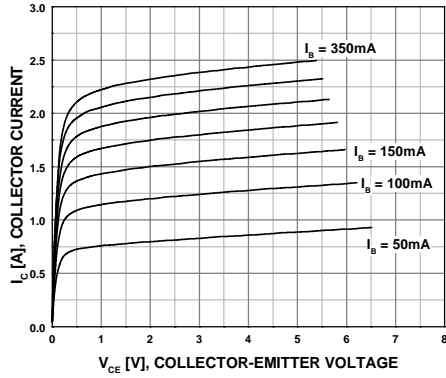


Figure 1. Static Characteristic

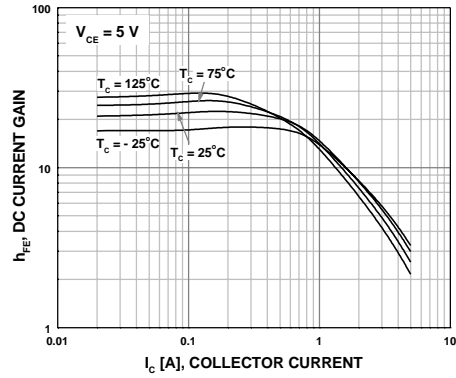


Figure 2. DC current Gain

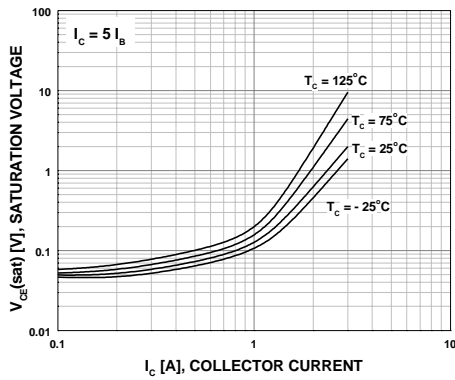


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

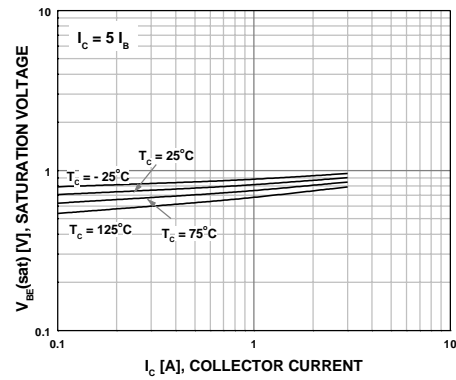


Figure 4. Base-Emitter On Voltage

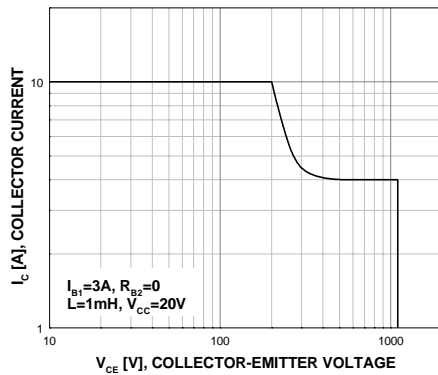


Figure 5. Switching Time

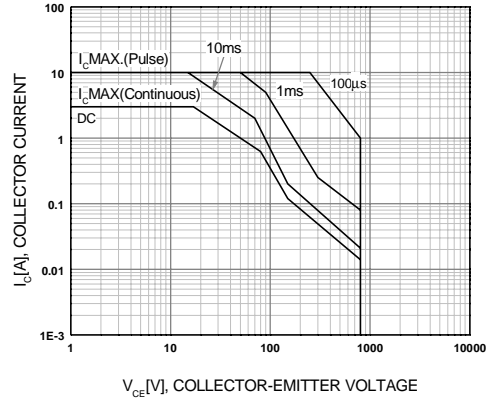


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

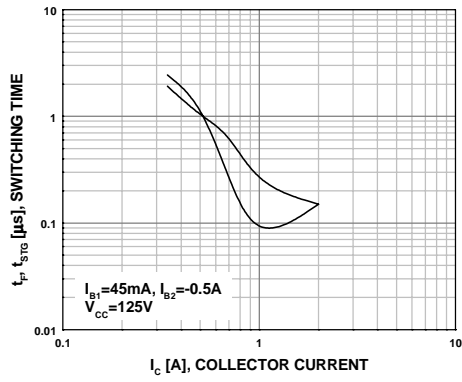


Figure 7. Resistive Load Switching Characteristics

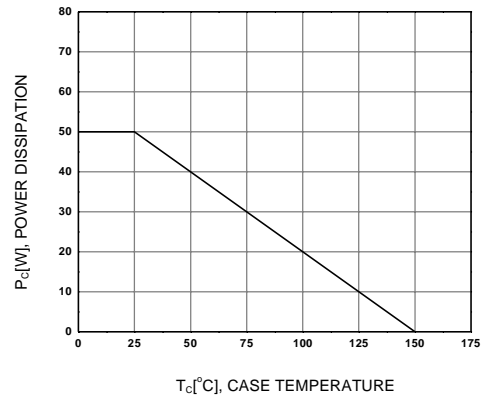
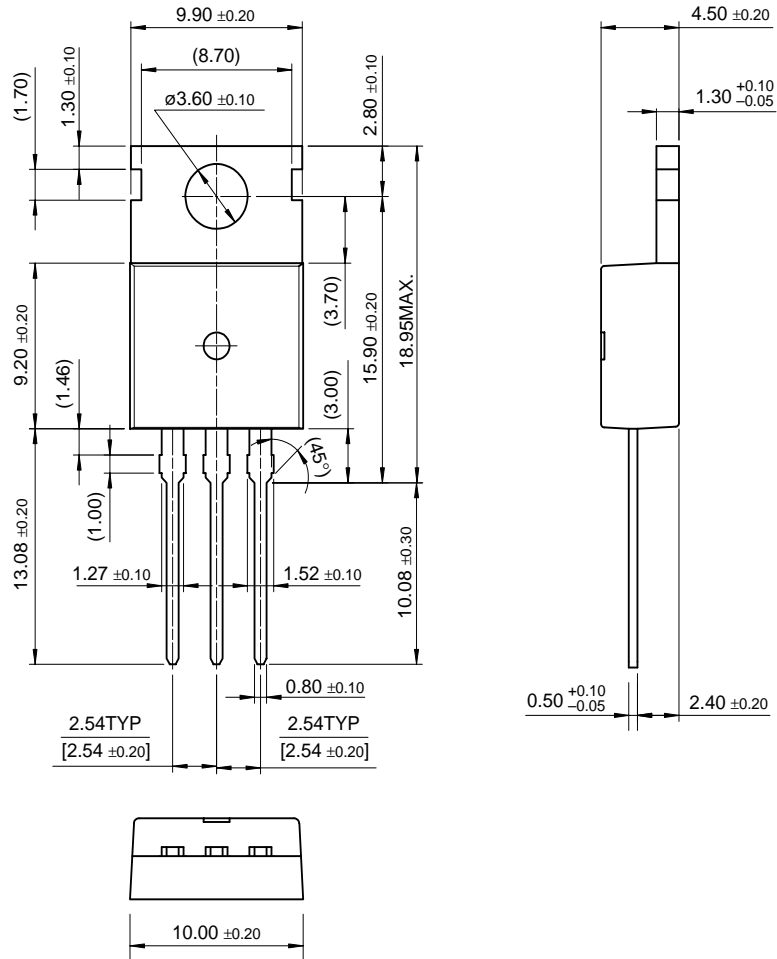


Figure 8. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

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